N0118GA

SCR

5 September 2018 Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier with ultra-sensitive gate in a SOT54 (TO-92) plastic package.

2. Features and benefits

- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

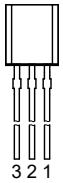
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67$ °C; Fig. 1		-	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67$ °C; Fig. 2; Fig. 3		-	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5		-	-	8	A
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms		-	-	9	A
T_j	junction temperature			-	-	125	°C
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 10$ mA; $T_j = 25$ °C; Fig. 7		0.5	-	7	µA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402$ V; $T_j = 125$ °C; $R_{GK} = 1$ kΩ; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 13; Fig. 14		75	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 TO-92 (SOT54)	 *sym037*
2	G	gate		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

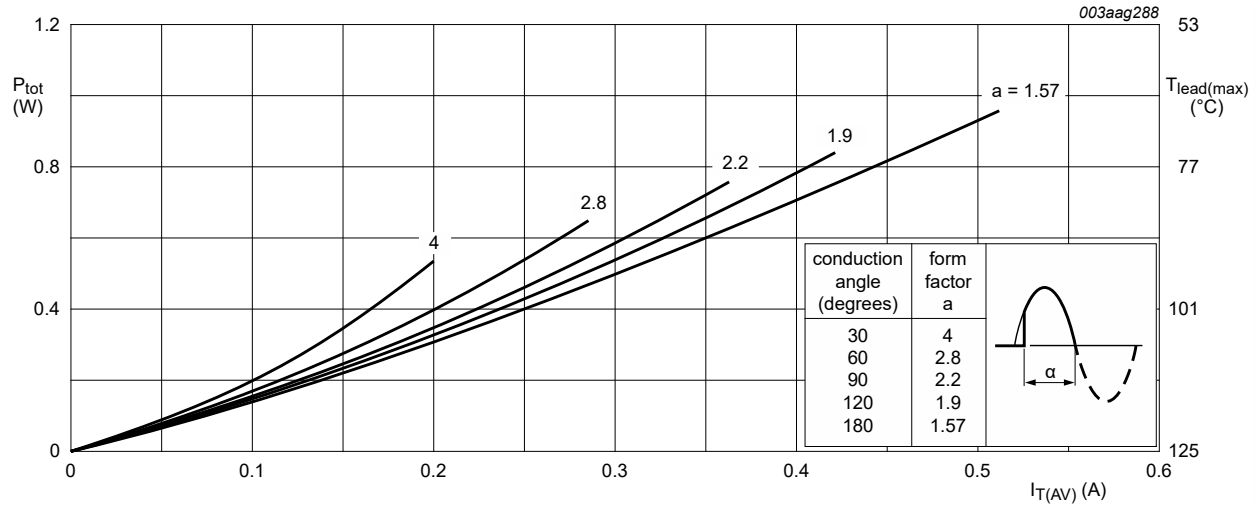
Type number	Package		
	Name	Description	Version
N0118GA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

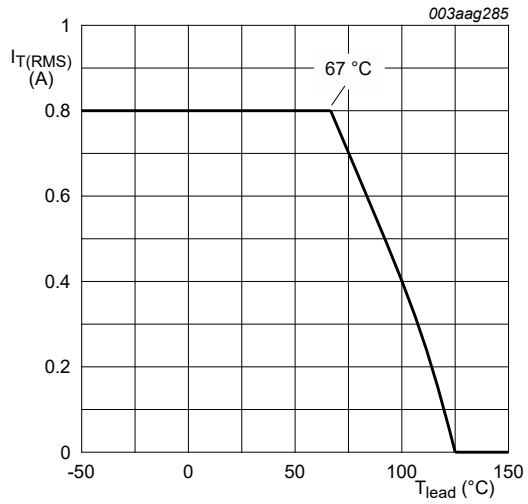
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67$ °C; Fig. 1		-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67$ °C; Fig. 2; Fig. 3		-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5		-	8	A
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms		-	9	A
I^2t	I^2t for fusing	$t_p = 10$ ms; SIN		-	0.32	A²s
dI_T/dt	rate of rise of on-state current	$I_T = 0.8$ A; $I_G = 10$ mA; $dI_G/dt = 0.1$ A/µs		-	50	A/µs
I_{GM}	peak gate current			-	1	A
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C



α = conduction angle

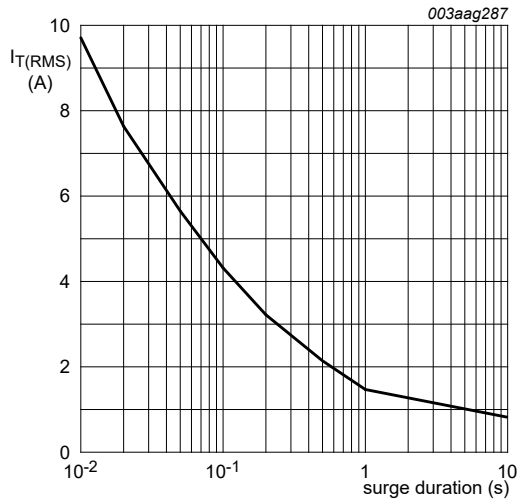
a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 1. Total power dissipation as a function of average on-state current; maximum values



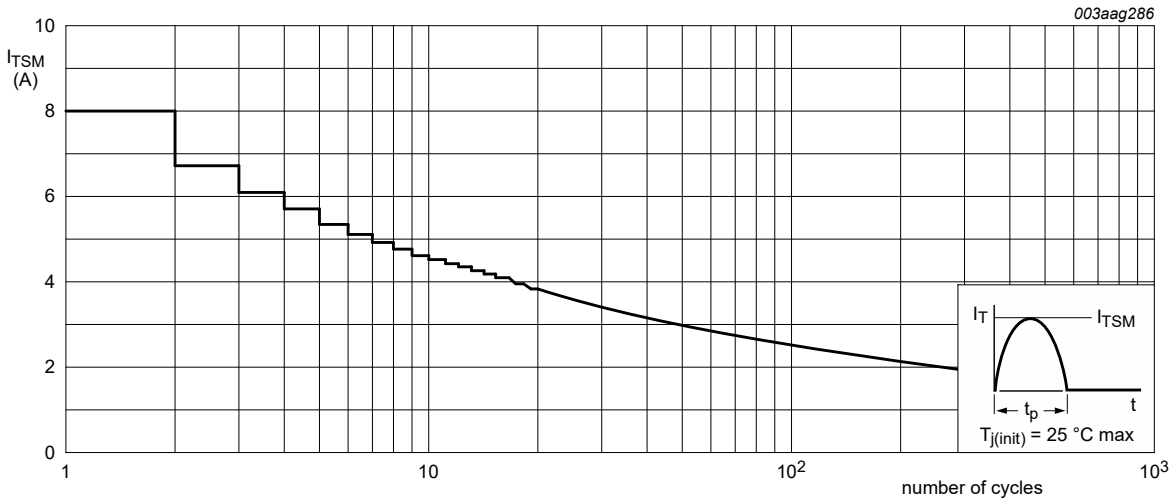
(1) T_{lead} = 67 °C

Fig. 2. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 67 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

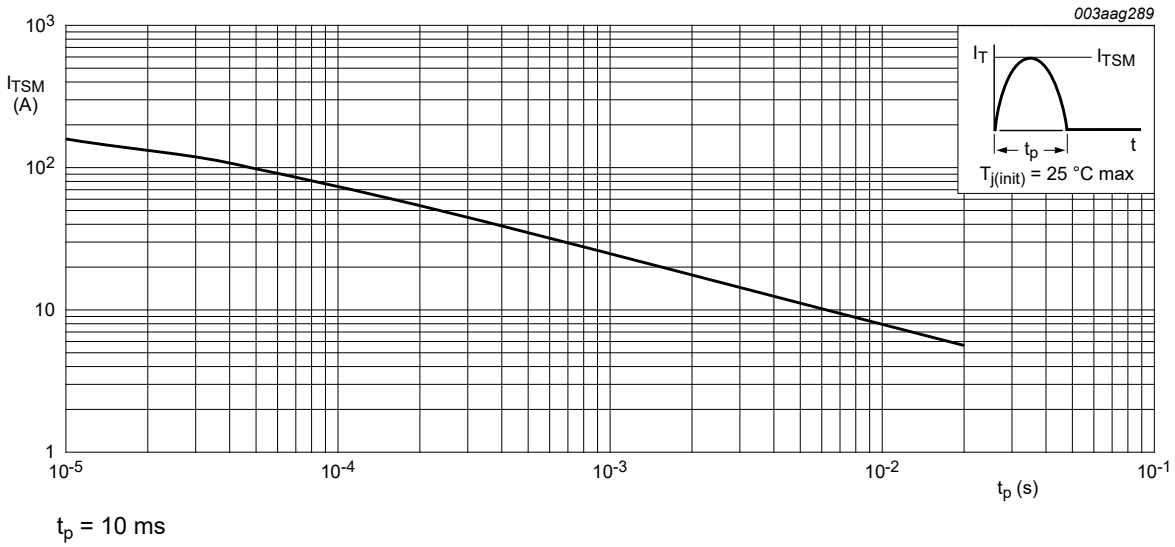


Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	Fig. 6		-	-	60	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm		-	150	-	K/W

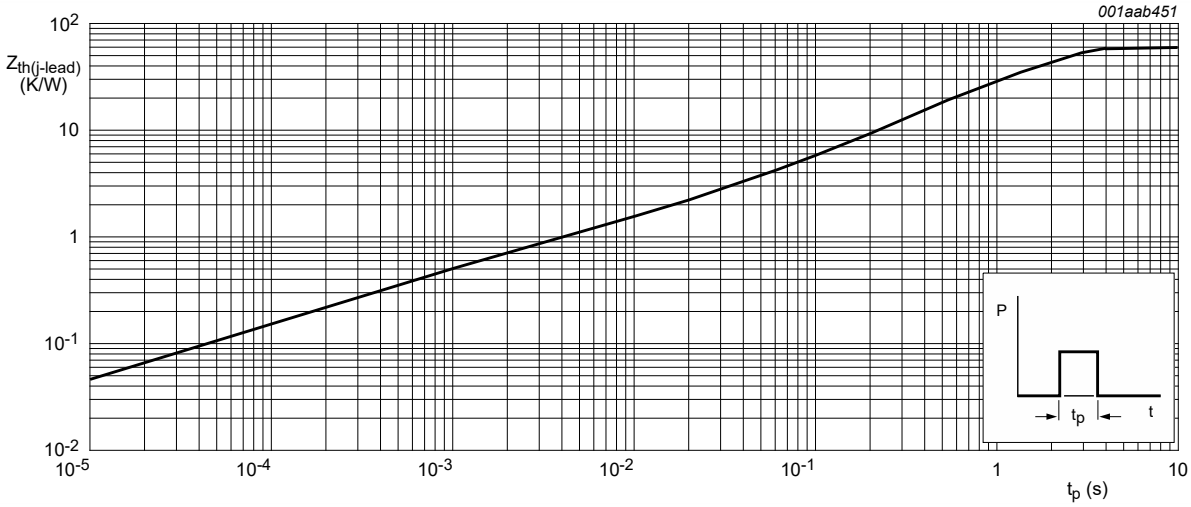


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 10 mA; T_j = 25 °C; Fig. 7		0.5	-	7	µA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T_j = 25 °C; Fig. 8		-	-	6	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9; Fig. 10		-	-	5	mA
V_T	on-state voltage	I_T = 1.6 A; T_j = 25 °C; Fig. 11		-	1.4	1.95	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 12		-	-	0.8	V
I_D	off-state current	V_D = 400 V; T_j = 25 °C		-	-	10	µA
		V_D = 600 V; $R_{GK(ext)}$ = 1 kΩ; T_j = 125 °C		-	-	100	µA
I_R	reverse current	V_R = 600 V; T_j = 25 °C; $R_{GK(ext)}$ = 1 kΩ		-	-	10	µA
		V_R = 600 V; T_j = 125 °C; $R_{GK(ext)}$ = 1 kΩ		-	-	100	µA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 1 kΩ; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 13; Fig. 14		75	-	-	V/µs

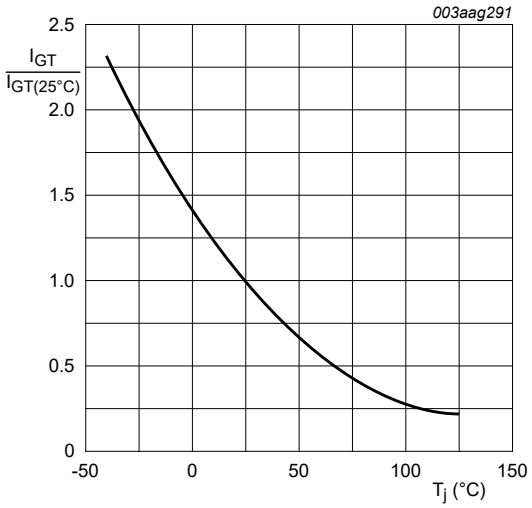
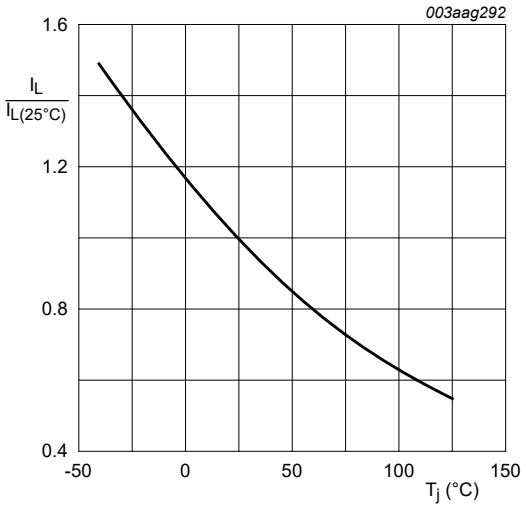
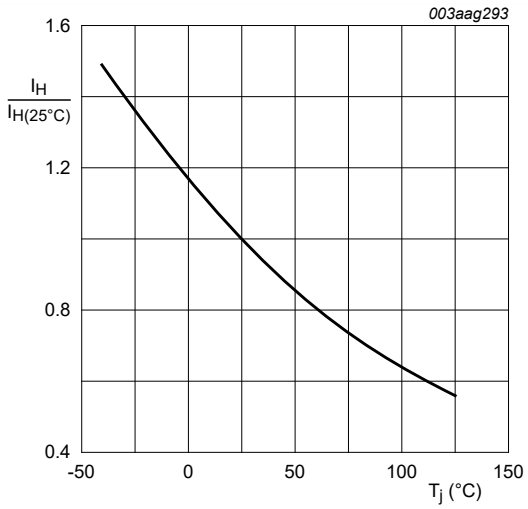


Fig. 7. Normalized gate trigger current as a function of junction temperature



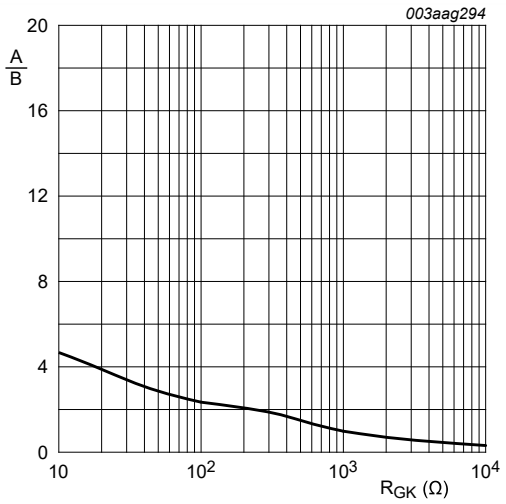
R_{GK} = 1 kΩ

Fig. 8. Normalized latching current as a function of junction temperature



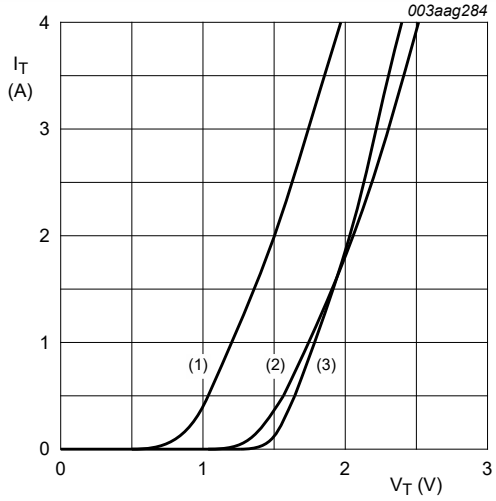
R_{GK} = 1 kΩ

Fig. 9. Normalized holding current as a function of junction temperature



A = I_H [R_{GK}]
B = I_H [R_{GK} = 1 kΩ]
T_j = 25 °C

Fig. 10. Normalized holding current as a function of gate-cathode resistance (typical values)



V_o = 1.383 V; R_s = 0.4 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

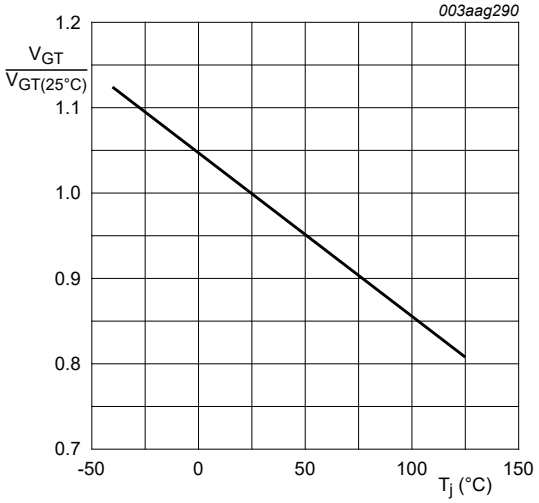
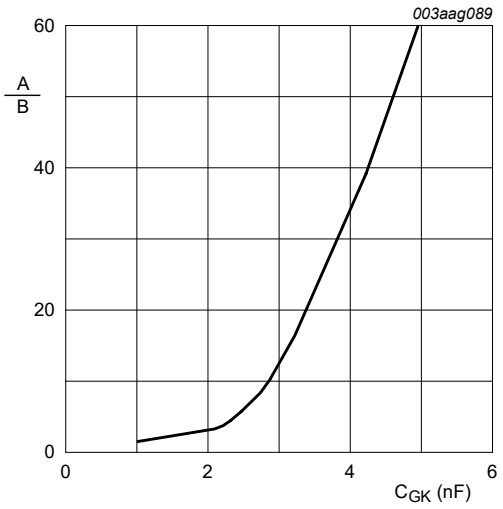
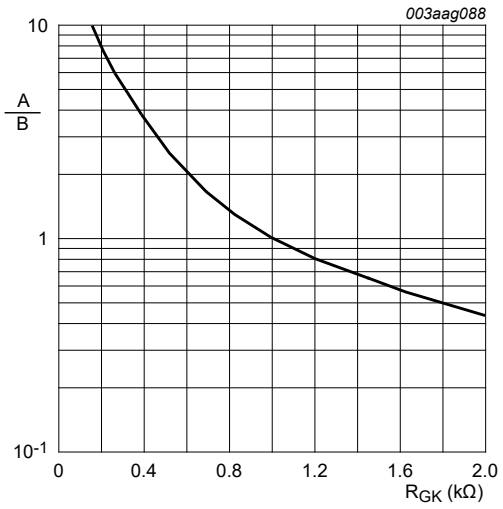


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



A = dV / dt [C_{GK}]
B = dV / dt [R_{GK} = 1 kΩ]
T_j = 125 °C;
R_{GK} = 1 kΩ; V_{DM} = 402 V

Fig. 13. Normalized dVd/dt immunity as a function of gate-cathode capacitance (typical values)



A = dV / dt [C_{GK}]
B = dV / dt [R_{GK} = 1 kΩ]
T_j = 125 °C;
R_{GK} = 1 kΩ; V_{DM} = 402 V

Fig. 14. Normalized dVd/dt immunity as a function of gate-cathode resistance (typical values)

10. Package outline

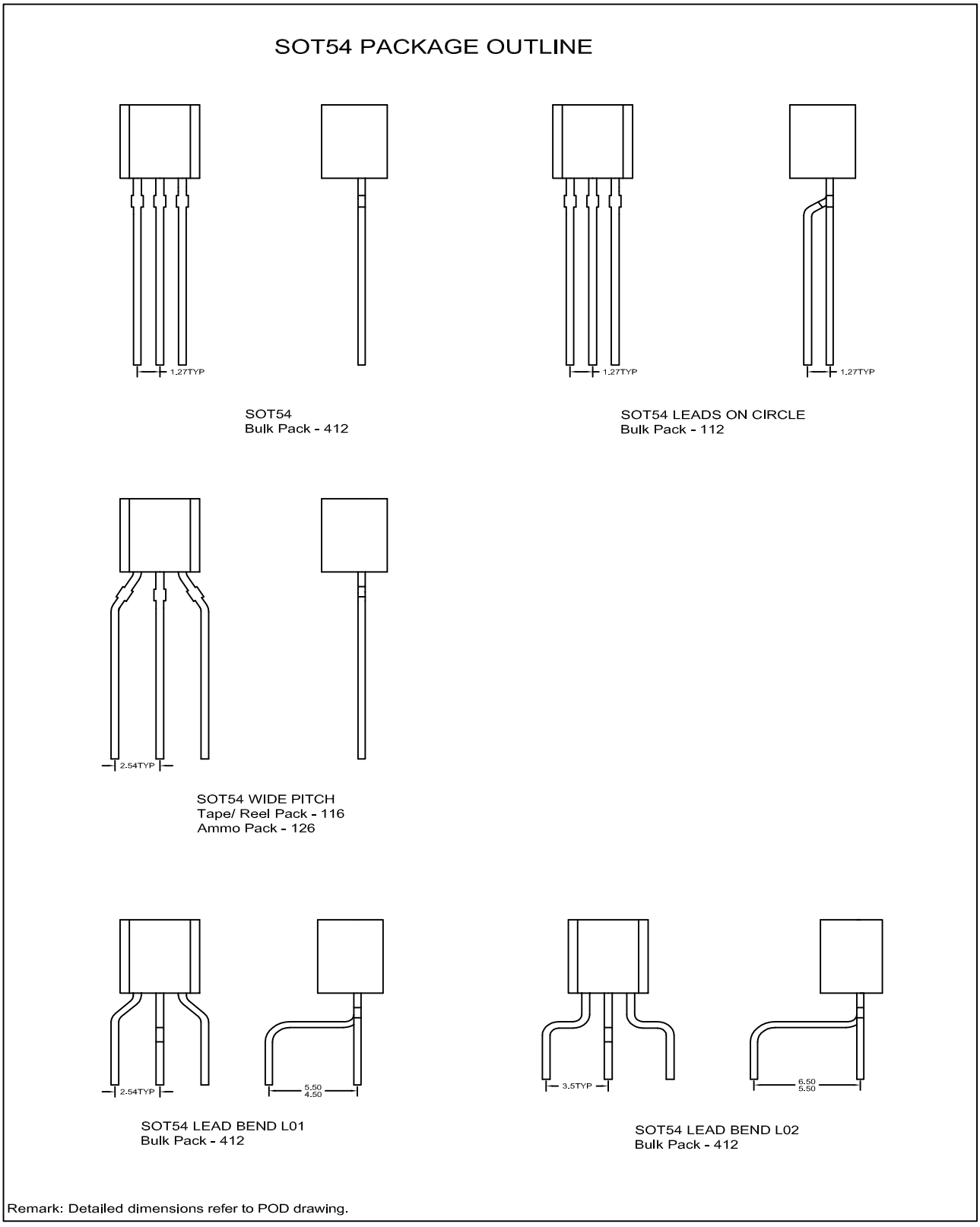


Fig. 15. Package outline TO-92 (SOT54)

11. Legal information

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Document status [1][2]	Product status [3]	Definition
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